Kazumasa Hiramatsu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

179 papers	7,143 citations	36 h-index	82 g-index
184 ext. papers	7,583 ext. citations	1.8 avg, IF	5.36 L-index

#	Paper	IF	Citations
179	Fabrication of perfect plasmonic absorbers for blue and near-ultraviolet lights using double-layer wire-grid structures. *Journal of the European Optical Society-Rapid Publications*, **2021**, 17,	2.5	2
178	Fabrication and characterization of a binary diffractive lens for controlling focal distribution. *Applied Optics*, **2020**, 59, 742-747	1.7	2
177	Fabrication and characterization of plasmonic band-stop filter using Ag grating. *EPJ Web of Conferences*, **2020**, 238, 05006	0.3	
176	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al0.61Ga0.39N Epitaxial Layer. *Physica Status Solidi (B): Basic Research*, **2018**, 255, 1700374	1.3	3
175	Cathodoluminescence study on local high-energy emissions at dark spots in AlGaN/AlGaN multiple quantum wells. *Japanese Journal of Applied Physics*, **2018**, 57, 060311	1.4	1
174	Effect of thermal annealing on AlN films grown on sputtered AlN templates by metalorganic vapor phase epitaxy. *Japanese Journal of Applied Physics*, **2018**, 57, 01AD05	1.4	35
173	Selective area growth of GaN on trench-patterned nonpolar bulk GaN substrates. *Journal of Crystal Growth*, **2017**, 468, 851-855	1.6	1
172	High-temperature photoluminescence and photoluminescence excitation spectroscopy of Al0.60Ga0.40N/Al0.70Ga0.30N multiple quantum wells. *Applied Physics Express*, **2017**, 10, 021002	2.4	7
171	Confinement-enhanced biexciton binding energy in AlGaN-based quantum wells. *Applied Physics Express*, **2017**, 10, 051003	2.4	2
170	Structural study of GaN grown on nonpolar bulk GaN substrates with trench patterns. *Japanese Journal of Applied Physics*, **2017**, 56, 125504	1.4	1
169	Excitation mechanism of surface plasmon polaritons in a double-layer wire grid structure. *Applied Physics A: Materials Science and Processing*, **2017**, 123, 1	2.6	5
168	Fabrication of high-crystallinity a -plane AlN films grown on r -plane sapphire substrates by modulating buffer-layer growth temperature and thermal annealing conditions. *Journal of Crystal Growth*, **2017**, 468, 845-850	1.6	16
167	Preparation of high-quality AlN on sapphire by high-temperature face-to-face annealing. *Journal of Crystal Growth*, **2016**, 456, 155-159	1.6	165
166	Annealing of an AlN buffer layer in N2‰O for growth of a high-quality AlN film on sapphire. *Applied Physics Express*, **2016**, 9, 025501	2.4	139
165	Microstructural analysis of an epitaxial AlN thick film/trench-patterned template by three-dimensional reciprocal lattice space mapping technique. *Applied Physics Express*, **2016**, 9, 111001	2.4	6
164	Impact of high-temperature annealing of AlN layer on sapphire and its thermodynamic principle. *Japanese Journal of Applied Physics*, **2016**, 55, 05FL02	1.4	36
163	Effect of surface pretreatment ofr-plane sapphire substrates on the crystal quality ofa-plane AlN. *Japanese Journal of Applied Physics*, **2016**, 55, 05FA12	1.4	3

162	Electron microscopy analysis of microstructure of postannealed aluminum nitride template. *Applied Physics Express*, **2016**, 9, 065502	2.4	8
161	Surface thermal stability of free-standing GaN substrates. *Japanese Journal of Applied Physics*, **2016**, 55, 01AC08	1.4	1
160	Effects of AlN buffer layer thickness on the crystallinity and surface morphology of 10-μm-thicka-plane AlN films grown onr-plane sapphire substrates. *Applied Physics Express*, **2016**, 9, 081001	2.4	8
159	HVPE homoepitaxy on freestanding AlN substrate with trench pattern. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2015**, 12, 334-337		3
158	Using surface-plasmon polariton at the GaP-Au interface in order to detect chemical species in high-refractive-index media. *Optics Communications*, **2015**, 341, 64-68	2	8
157	Fabrication of AlGaN multiple quantum wells on sapphire with lattice-relaxation layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2015**, 12, 361-364		
156	Growth Characteristics of Graphene Film by Chemical Vapor Deposition Method Using Nozzle Gas Injection. *E-Journal of Surface Science and Nanotechnology*, **2015**, 13, 265-268	0.7	
155	Study on AlN growth conditions for hydride vapor phase epitaxy. *Transactions of the Materials Research Society of Japan*, **2015**, 40, 395-396	0.2	
154	Excitation-dependent carrier dynamics in Al-rich AlGaN layers and multiple quantum wells. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 1043-1049	1.3	3
153	Extraordinary Optical Transmission Exhibited by Surface Plasmon Polaritons in a Double-Layer Wire Grid Polarizer. *Plasmonics*, **2015**, 10, 1657-1662	2.4	13
152	Fabrication and optical characterization of a 2D metal periodic grating structure for cold filter application **2015**,		1
151	Selective-area growth of GaN on non- and semi-polar bulk GaN substrates. *Japanese Journal of Applied Physics*, **2014**, 53, 05FL04	1.4	7
150	Inhomogeneous distribution of defect-related emission in Si-doped AlGaN epitaxial layers with different Al content and Si concentration. *Journal of Applied Physics*, **2014**, 115, 053509	2.5	19
149	Binding energy of localized biexcitons in AlGaN-based quantum wells. *Applied Physics Express*, **2014**, 7, 122101	2.4	7
148	Anisotropic crystalline morphology of epitaxial thick AlN films grown on triangular-striped AlN/sapphire template. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 731-735	1.6	3
147	Transient photoluminescence of aluminum-rich (Al,Ga)N low-dimensional structures. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 765-768	1.6	5
146	Local Strain Distribution in AlN Thick Films Analyzed by X-Ray Microdiffraction. *Materials Science Forum*, **2014**, 783-786, 2016-2021	0.4	
145	MOVPE growth of GaN on Si substrate with 3C-SiC buffer layer. *Japanese Journal of Applied Physics*, **2014**, 53, 05FL09	1.4	14

144	High-quality AlN growth on 6H-SiC substrate using three dimensional nucleation by low-pressure hydride vapor phase epitaxy. *Japanese Journal of Applied Physics*, **2014**, 53, 05FL03	1.4	22
143	Si concentration dependence of structural inhomogeneities in Si-doped AlxGa1−xN/AlyGa1−yN multiple quantum well structures (x = 0.6) and its relationship with internal quantum efficiency. *Journal of Applied Physics*, **2014**, 116, 235703	2.5	4
142	Study on the effects of AlN interlayer in thick GaN grown on 3C-SiC/Si substrates. *Journal of Crystal Growth*, **2013**, 370, 254-258	1.6	4
141	Effects of Si doping in high-quality AlN grown by MOVPE on trench-patterned template. *Journal of Crystal Growth*, **2013**, 370, 74-77	1.6	3
140	Cathodoluminescence Study of Optical Inhomogeneity in Si-Doped AlGaN Epitaxial Layers Grown by Low-Pressure Metalorganic Vapor-Phase Epitaxy. *Japanese Journal of Applied Physics*, **2013**, 52, 08JL07	1.4	4
139	Selective Area Growth of Semipolar (202 1) and (202 1) GaN Substrates by Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2013**, 52, 08JC06	1.4	5
138	AlN Grown ona- andn-Plane Sapphire Substrates by Low-Pressure Hydride Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2013**, 52, 08JB31	1.4	10
137	Realization of Maskless Epitaxial Lateral Overgrowth of GaN on 3C-SiC/Si Substrates. *Japanese Journal of Applied Physics*, **2013**, 52, 08JB07	1.4	6
136	Growth and Characterization of AlGaN Multiple Quantum Wells for Electron-Beam Target for Deep-Ultraviolet Light Sources. *Japanese Journal of Applied Physics*, **2013**, 52, 01AF03	1.4	23
135	Fabrication of Binary Diffractive Lenses and the Application to LED Lighting for Controlling Luminosity Distribution. *Optics and Photonics Journal*, **2013**, 03, 67-73	0.3	8
134	The Application of Local Traditional Crafts to a New LED Lighting System : The Development of an LED Lighting System with Human Sensitivity Using Ise Paper Stencils as Lamp Shades(Tokai Branch, Create the New Technology Fits the Occasion with the Succession of Arts). *Journal of the Illuminating Engineering Institute of Japan (Shomei Gakkai Shi)*, **2013**, 97, 381-385	0.1	
133	Correlation between in-plane strain and optical polarization of Si-doped AlGaN epitaxial layers as a function of Al content and Si concentration. *Journal of Applied Physics*, **2012**, 112, 033512	2.5	8
132	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. *Journal of Crystal Growth*, **2012**, 350, 69-71	1.6	14
131	Orientation dependence of polarized Raman spectroscopy for nonpolar, semi-polar, and polar bulk GaN substrates. *Applied Physics Letters*, **2012**, 100, 011909	3.4	10
130	Effects of carrier gas ratio and growth temperature on MOVPE growth of AlN. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 499-502		12
129	Fabrication of crack-free thick AlN film on a-plane sapphire by low-pressure HVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 576-579		7
128	Photoluminescence due to Inelastic Biexciton Scattering from an Al$_{0.61}$Ga$_{0.39}$N Ternary Alloy Epitaxial Layer at Room Temperature. *Applied Physics Express*, **2012**, 5, 072401	2.4	8
127	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGaN quantum wells. *Applied Physics Letters*, **2012**, 101, 042110	3.4	37

126	Observation of longitudinal-optic-phonon-plasmon-coupled mode in n-type AlGaN alloy films. *Applied Physics Letters*, **2011**, 99, 251904	3.4	5
125	HVPE growth of c-plane AlN on a-plane sapphire using nitridation layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 470-472		6
124	HVPE growth of AlN on trench- patterned 6H-SiC substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 467-469		9
123	Recombination dynamics of localized excitons in AlxGa1-xN (0.37. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2133-2135		5
122	Evidence for moving of threading dislocations during the VPE growth in GaN thin layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1487-1490		4
121	HVPE growth of thick AlN on trench-patterned substrate. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1483-1486		7
120	Stress analysis of a-plane GaN grown on r-plane sapphire substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2066-2068		
119	Control of AlN buffer/sapphire substrate interface for AlN growth. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2069-2071		16
118	Raman Scattering Spectroscopy of Residual Stresses in Epitaxial AlN Films. *Applied Physics Express*, **2011**, 4, 031001	2.4	54
117	Huge binding energy of localized biexcitons in Al-rich AlxGa1□N ternary alloys. *Applied Physics Letters*, **2011**, 98, 081907	3.4	8
116	Silicon concentration dependence of optical polarization in AlGaN epitaxial layers. *Applied Physics Letters*, **2011**, 98, 021910	3.4	14
115	Fabrication of Deep-Ultraviolet-Light-Source Tube Using Si-Doped AlGaN. *Applied Physics Express*, **2011**, 4, 042103	2.4	52
114	Growth of High-Quality Si-Doped AlGaN by Low-Pressure Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 095502	1.4	13
113	Growth of High-Quality Si-Doped AlGaN by Low-Pressure Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 095502	1.4	10
112	Variation of Surface Potentials of Si-Doped AlxGa1-xN (0 . *Applied Physics Express*, **2010**, 3, 021004	2.4	5
111	Deep Electronic Levels of AlxGa1-xN with a Wide Range of Al Composition Grown by Metal□rganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2010**, 49, 101001	1.4	9
110	Study of High-Quality and Crack-Free GaN Growth on 3C-SiC/Separation by Implanted Oxygen (111). *Japanese Journal of Applied Physics*, **2010**, 49, 041001	1.4	5
109	In-plane structural anisotropy and polarized Raman-active mode studies of nonpolar AlN grown on 6H-SiC by low-pressure hydride vapor phase epitaxy. *Journal of Crystal Growth*, **2010**, 312, 490-494	1.6	7

108	Formation mechanism of Al-depleted bands in MOVPE-AlGaN layer on GaN template with trenches. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2036-2039		
107	a -plane AlN and AlGaN growth on r -plane sapphire by MOVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2107-2110		5
106	In-plane electric field induced by polarization and lateral photovoltaic effect in a-plane GaN. *Applied Physics Letters*, **2009**, 94, 231102	3.4	7
105	Growth of High Quality c-plane AlN on a-plane Sapphire. *Materials Research Society Symposia Proceedings*, **2009**, 1202, 55		1
104	Facet-control in selective area growth (SAG) of a-plane GaN by MOVPE. *Materials Research Society Symposia Proceedings*, **2009**, 1202, 98		
103	Fabrication of a binary diffractive lens for controlling the luminous intensity distribution of LED light. *Optical Review*, **2009**, 16, 455-457	0.9	6
102	Effects of initial conditions and growth temperature on the properties of nonpolar a -plane AlN grown by LP-HVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S478-S481		5
101	Structural and electrical properties of Si-doped a-plane GaN grown on r-plane sapphire by MOVPE. *Journal of Crystal Growth*, **2009**, 311, 2899-2902	1.6	18
100	Photoluminescence study of Si-doped a-plane GaN grown by MOVPE. *Journal of Crystal Growth*, **2009**, 311, 2906-2909	1.6	19
99	Optical properties of MOVPE-grown a-plane GaN and AlGaN. *Journal of Crystal Growth*, **2009**, 311, 2903-2905	1.6	9
98	Effects of initial stages on the crystal quality of nonpolar a-plane AlN on r-plane sapphire by low-pressure HVPE. *Journal of Crystal Growth*, **2009**, 311, 3801-3805	1.6	18
97	Influence of off-cut angle of r-plane sapphire on the crystal quality of nonpolar a-plane AlN by LP-HVPE. *Journal of Crystal Growth*, **2009**, 311, 4473-4477	1.6	17
96	Effects of Substrate Plane on the Growth of High Quality AlN by Hydride Vapor Phase Epitaxy. *Applied Physics Express*, **2009**, 2, 111004	2.4	16
95	Nitridating r-plane sapphire to improve crystal qualities and surface morphologies of a-plane GaN grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **2009**, 95, 121910	3.4	19
94	Thermal analysis of GaN powder formation via reaction of gallium ethylenediamine tetraacetic acid complexes with ammonia. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1522-1524		1
93	Improved surface morphology of flow-modulated MOVPE grown AlN on sapphire using thin medium-temperature AlN buffer layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1818-1821		0
92	Improved optical properties of AlGaN using periodic structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1822-1824		1
91	Optical Characterization of Japanese Papers for Application in the LED Lighting System with Human Sensitivity. *Journal of Light and Visual Environment*, **2008**, 32, 218-221		1

90	Selective Area Growth of III-Nitride and Their Application for Emitting Devices. *Journal of Light and Visual Environment*, **2008**, 32, 177-182		
89	Fundamental Properties of Wide Bandgap Semiconductors **2007**, 25-96		
88	Influence of growth conditions on Al incorporation to AlxGa1⊠N (x>0.4) grown by MOVPE. *Journal of Crystal Growth*, **2007**, 298, 372-374	1.6	13
87	Influence of growth interruption and Si doping on the structural and optical properties of AlxGaN/AlN (x>0.5) multiple quantum wells. *Journal of Crystal Growth*, **2007**, 298, 500-503	1.6	14
86	Structural and optical properties of Si-doped AlGaN/AlN multiple quantum wells grown by MOVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2494-2497		
85	Blue emission from InGaN/GaN hexagonal pyramid structures. *Superlattices and Microstructures*, **2007**, 41, 341-346	2.8	9
84	Suppression of Crack Generation Using High-Compressive-Strain AlN/Sapphire Template for Hydride Vapor Phase Epitaxy of Thick AlN Film. *Japanese Journal of Applied Physics*, **2007**, 46, L552-L555	1.4	14
83	Growth characteristics of carbon nanotubes on nanotip-formed substrate. *Journal of Vacuum Science & Technology B*, **2006**, 24, 1004		1
82	Enhanced emission efficiency of InGaN films with Si doping. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1944-1948		3
81	Fabrication of thick AlN film by low pressure hydride vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1479-1482		5
80	n-type conductivity control of AlGaN with high Al mole fraction. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1435-1438		4
79	Enhancement of blue emission from Mg-doped GaN activated at low temperature in O2/N2 mixture. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 2750-2753		2
78	Influence of Si doping on the optical and structural properties of InGaN films. *Journal of Crystal Growth*, **2006**, 290, 374-378	1.6	4
77	Growth control of carbon nanotubes by plasma-enhanced chemical vapor deposition and reactive ion etching. *Vacuum*, **2006**, 80, 798-801	3.7	4
76	Growth of Thick AlN Layer by Hydride Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2005**, 44, L505-L507	1.4	35
75	Fabrication and characterization of UV Schottky detectors by using a freestanding GaN substrate. *Materials Research Society Symposia Proceedings*, **2004**, 831, 359		
74	Reduction of dislocation density in AlGaN with high AlN molar fraction by using a rugged AlN epilayer. *Materials Research Society Symposia Proceedings*, **2004**, 831, 353		2
73	Metalorganic Vapor Phase Epitaxy Growth and Study of Stress in AlGaN Using Epitaxial AlN as Underlying Layer. *Japanese Journal of Applied Physics*, **2003**, 42, L572-L574	1.4	10

72	Epitaxial lateral overgrowth of GaN on selected-area Si(1 1 1) substrate with nitrided Si mask. *Journal of Crystal Growth*, **2003**, 248, 573-577	1.6	10
71	Characterization of GaN based Schottky UV detectors in the vacuum UV (VUV) and the soft X-ray (SX) region (10–100 nm). *Physica Status Solidi A*, **2003**, 200, 147-150		6
70	MOVPE growth and n-type conductivity control of high-quality Si-doped Al0.5Ga0.5N using epitaxial AlN as an underlying layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2128-2131		1
69	Characterization of III-nitride Based Schottky UV Detectors with Wide Detectable Wavelength Range (360–10 nm) using Synchrotron Radiation. *Materials Research Society Symposia Proceedings*, **2003**, 798, 683		
68	Antireflection Effect of Self-Organized GaN Nanotip Structure from Ultraviolet to Visible Region. *Japanese Journal of Applied Physics*, **2002**, 41, L1134-L1136	1.4	12
67	Transmission Electron Microscopy Investigation of Dislocations in GaN Layer Grown by Facet-Controlled Epitaxial Lateral Overgrowth. *Japanese Journal of Applied Physics*, **2001**, 40, L309-L312	1.4	24
66	Characterization of GaN-Based Schottky Barrier Ultraviolet (UV) Detectors in the UV and Vacuum Ultraviolet (VUV) Region Using Synchrotron Radiation. *Japanese Journal of Applied Physics*, **2001**, 40, L368-L370	1.4	12
65	Formation of GaN Self-Organized Nanotips by Reactive Ion Etching. *Japanese Journal of Applied Physics*, **2001**, 40, L1301-L1304	1.4	51
64	In Situ Monitoring of GaN Reactive Ion Etching by Optical Emission Spectroscopy. *Japanese Journal of Applied Physics*, **2001**, 40, L313-L315	1.4	8
63	Sharp band edge photoluminescence of high-purity CuInS2 single crystals. *Applied Physics Letters*, **2001**, 78, 742-744	3.4	74
62	Effects of buffer layers and advanced technologies on heteroepitaxy of GaN **2001**, 210-232		2
61	Epitaxial lateral overgrowth techniques used in group III nitride epitaxy. *Journal of Physics Condensed Matter*, **2001**, 13, 6961-6975	1.8	79
60	Effects of the Schottky electrode structure in GaN based UV-VUV (50-360 nm) photodetector. *Materials Research Society Symposia Proceedings*, **2001**, 693, 230		
59	Effect of Ge in Cl2 Plasma for Reactive Ion Etching of GaN. *Materials Research Society Symposia Proceedings*, **2001**, 693, 174		
58	New buffer layer technique using underlying epitaxial AlN films for high-quality GaN growth. *Materials Research Society Symposia Proceedings*, **2001**, 693, 501		
57	Characterization of high-quality epitaxial AlN films grown by MOVPE. *Materials Research Society Symposia Proceedings*, **2001**, 693, 774		4
56	TEM Analysis of Threading Dislocations in ELO-GaN Grown with Controlled Facet Planes. *Materials Research Society Symposia Proceedings*, **2000**, 639, 11591		3
55	Fabrication and characterization of low defect density GaN using facet-controlled epitaxial lateral overgrowth (FACELO). *Journal of Crystal Growth*, **2000**, 221, 316-326	1.6	364

54	Epitaxial Growth and Dislocation Formation in Crystals of Nitride Semiconductors. *Hyomen Kagaku*, **2000**, 21, 155-161		
53	Fabrication of GaN with Buried Tungsten (W) Structures Using Epitaxial Lateral Overgrowth (ELO) via LP-MOVPE. *MRS Internet Journal of Nitride Semiconductor Research*, **2000**, 5, 62-68		1
52	Gradual tilting of crystallographic orientation and configuration of dislocations in GaN selectively grown by vapour phase epitaxy methods. *Journal of Electron Microscopy*, **2000**, 49, 331-8		10
51	Review of Facet Controlled Epitaxial Lateral Overgrowth (FACELO) of GaN via Low Pressure Vapor Phase Epitaxy. *Materials Research Society Symposia Proceedings*, **2000**, 639, 841		1
50	Defect structure in selective area growth GaN pyramid on (111)Si substrate. *Applied Physics Letters*, **2000**, 76, 2701-2703	3.4	75
49	Selective Area Growth (SAG) and Epitaxial Lateral Overgrowth (ELO) of GaN using Tungsten Mask. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 441-446		1
48	Hydrogen and Nitrogen Ambient Effects on Epitaxial Lateral Overgrowth (ELO) of GaN VIA Metalorganic Vapor-Phase Epitaxy (Movpe). *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 118-123		3
47	Optical and Crystalline Properties of Epitaxial-Lateral-Overgrown-GaN Using Tungsten Mask by Hydride Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1999**, 38, L356-L359	1.4	60
46	Crystal Orientation Fluctuation of Epitaxial-Lateral-Overgrown GaN with W Mask and SiO2 Mask Observed by Transmission Electron Diffraction and X-Ray Rocking Curves. *Japanese Journal of Applied Physics*, **1999**, 38, L1299-L1302	1.4	18
45	Selective area growth and epitaxial lateral overgrowth of GaN by metalorganic vapor phase epitaxy and hydride vapor phase epitaxy. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 59, 104-111	3.1	17
44	Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1999**, 38, L1000-L1002	1.4	88
43	Fabrication of GaN with Buried Tungsten (W) Structures Using Epitaxial Lateral Overgrowth (ELO) via LP-MOVPE. *Materials Research Society Symposia Proceedings*, **1999**, 595, 1		1
42	The formation of crystalline defects and crystal growth mechanism in InxGa1−xN/GaN heterostructure grown by metalorganic vapor phase epitaxy. *Journal of Crystal Growth*, **1998**, 189-190, 24-28	1.6	55
41	Hydride vapor-phase epitaxy growth of high-quality GaN bulk single crystal by epitaxial lateral overgrowth. *Journal of Crystal Growth*, **1998**, 189-190, 67-71	1.6	39
40	Sub-micron fine structure of GaN by metalorganic vapor phase epitaxy (MOVPE) selective area growth (SAG) and buried structure by epitaxial lateral overgrowth (ELO). *Journal of Crystal Growth*, **1998**, 189-190, 78-82	1.6	20
39	Selective Area Growth of GaN Using Tungsten Mask by Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1998**, 37, L845-L848	1.4	35
38	Selective Area Growth of GaN on Si Substrate Using SiO 2 Mask by Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1998**, 37, L966-L969	1.4	61
37	Hydrogen and Nitrogen Ambient Effects on Epitaxial Lateral Overgrowth (ELO) of GaN Via Metalorganic Vapor-Phase Epitaxy (MOVPE). *Materials Research Society Symposia Proceedings*, **1998** , 537, 1		5

36	Selective Area Growth (SAG) and Epitaxial Lateral Overgrowth (ELO) of GaN Using Tungsten Mask. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1		2
35	Metalorganic Vapor Phase Epitaxy of Thick InGaN on Sapphire Substrate. *Japanese Journal of Applied Physics*, **1997**, 36, 3381-3384	1.4	41
34	MOVPE growth of thick homogeneous InGaN directly on sapphire substrate using AlN buffer layer. *Solid-State Electronics*, **1997**, 41, 145-147	1.7	36
33	A study on barrier height of Au?AlxGa1 xN Schottky diodes in the range 0 x 0.20. *Solid-State Electronics*, **1997**, 41, 287-294	1.7	32
32	The Composition Pulling Effect in InGaN Growth on the GaN and AlGaN Epitaxial Layers Grown by MOVPE. *Materials Research Society Symposia Proceedings*, **1996**, 449, 89		38
31	Raman scattering study of the immiscible region in InGaAsP grown by LPE on (100) and (111) GaAs. *Journal of Electronic Materials*, **1996**, 25, 695-699	1.9	1
30	Fabrication of GaN Hexagonal Pyramids on Dot-Patterned GaN/Sapphire Substrates via Selective Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1995**, 34, L1184-L1186	1.4	161
29	Facets Formation Mechanism of GaN Hexagonal Pyramids on Dot-Patterns via Selective MOVPE. *Materials Research Society Symposia Proceedings*, **1995**, 395, 267		16
28	Selective growth of wurtzite GaN and AlxGa1 N on GaN/sapphire substrates by metalorganic vapor phase epitaxy. *Journal of Crystal Growth*, **1994**, 144, 133-140	1.6	278
27	Metalorganic vapor phase epitaxy growth of (InxGa1-xN/GaN)n layered structures and reduction of indium droplets. *Journal of Crystal Growth*, **1994**, 145, 209-213	1.6	50
26	Raman Scattering of InGaAsP Lattice-Matched to GaAs in the Region of Immiscibility. *Japanese Journal of Applied Physics*, **1993**, 32, 2718-2721	1.4	11
25	Relaxation Mechanism of Thermal Stresses in the Heterostructure of GaN Grown on Sapphire by Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1993**, 32, 1528-1533	1.4	190
24	Relaxation Process of the Thermal Strain in the GaN/Al2O3Heterostructure and Determination of the Intrinsic Lattice Constants of GaN Free from the Strain. *Japanese Journal of Applied Physics*, **1992**, 31, L1454-L1456	1.4	236
23	MOVPE growth of GaN on a misoriented sapphire substrate. *Journal of Crystal Growth*, **1991**, 107, 509-512	1.6	49
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